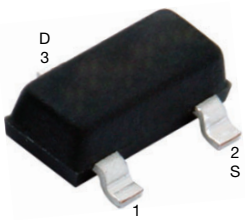
P-Channel 20 V (D-S) MOSFET

SOT-23 (TO-236)



Top View

Marking Code: P6

FEATURES

- TrenchFET® power MOSFET
- 100% R_g tested
- Typical ESD performance 2000 V
- Built in ESD protection with Zener Diode
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

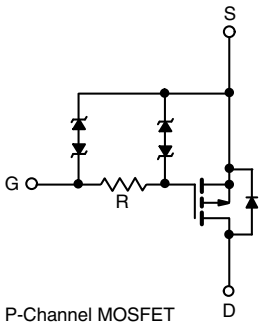
Pb-free

RoHS COMPLIANT

HALOGEN FREE

APPLICATIONS

- Load switch for portable devices



P-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	-20
$R_{DS(on)}$ max. (Ω) at V_{GS} = -4.5 V	0.061
$R_{DS(on)}$ max. (Ω) at V_{GS} = -2.5 V	0.080
$R_{DS(on)}$ max. (Ω) at V_{GS} = -1.8 V	0.110
$R_{DS(on)}$ max. (Ω) at V_{GS} = -1.5 V	0.165
Q_g typ. (nC)	7.6
I_D (A) [a]	-4.4
Configuration	Single

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	Si2377EDS-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-20	V
Gate-source voltage		V_{GS}	± 8	
Continuous drain current (T_J = 150 °C)	T_C = 25 °C	I_D	-4.4	A
	T_C = 70 °C		3.5	
	T_A = 25 °C		-3.7 [b, c]	
	T_A = 70 °C		-2.9 [b, c]	
Pulsed drain current		I_{DM}	-20	
Continuous source-drain diode current	T_C = 25 °C	I_S	-1.5	
	T_A = 25 °C		-1 [b, c]	
Maximum power dissipation	T_C = 25 °C	P_D	1.8	W
	T_C = 70 °C		1.1	
	T_A = 25 °C		1.25 [b, c]	
	T_A = 70 °C		0.8 [b, c]	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) [d, e]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient [b, d]	t ≤ 5 s	R_{thJA}	80	100	°C/W
Maximum junction-to-foot (drain)	Steady state	R_{thJF}	55	70	

Notes

a. T_C = 25 °C

b. Surface mounted on 1" x 1" FR4 board

c. t = 5 s

d. Maximum under steady state conditions is 130 °C/W

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SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 µA	-20	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	I_D = -250 µA	-	-13	-	mV/°C
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	2.5	-	
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA	-0.4	-	-1	V
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V	-	-	± 6	µA
		V_{DS} = 0 V, V_{GS} = ± 4.5 V	-	-	± 0.5	
Zero gate voltage drain current	I_{DSS}	V_{DS} = -20 V, V_{GS} = 0 V	-	-	-1	
		V_{DS} = -20 V, V_{GS} = 0 V, T_J = 55 °C	-	-	-10	
On-state drain current [a]	$I_{D(on)}$	V_{DS} ≤ -5 V, V_{GS} = -4.5 V	-15	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = -4.5 V, I_D = -3.2 A	-	0.050	0.061	Ω
		V_{GS} = -2.5 V, I_D = -2.8 A	-	0.065	0.080	
		V_{GS} = -1.8 V, I_D = -1.5 A	-	0.090	0.110	
		V_{GS} = -1.5 V, I_D = -0.5 A	-	0.110	0.165	
Forward transconductance [a]	g_{fs}	V_{DS} = -10 V, I_D = -3.2 A	-	12	-	S
Dynamic [b]						
Total gate charge	Q_g	V_{DS} = -10 V, V_{GS} = -8 V, I_D = -5.3 A	-	14	21	nC
		V_{DS} = -10 V, V_{GS} = -4.5 V, I_D = -5.3 A	-	7.6	12	
Gate-source charge	Q_{gs}		-	0.8	-	
Gate-drain charge	Q_{gd}		-	3.1	-	
Gate resistance	R_g	f = 1 MHz	0.4	2	4	kΩ
Turn-on delay time	$t_{d(on)}$	V_{DD} = -10 V, R_L = 2.3 Ω I_D ≅ -4.3 A, V_{GEN} = -4.5 V, R_g = 1 Ω	-	0.2	0.3	µs
Rise time	t_r		-	1	1.5	
Turn-off delay time	$t_{d(off)}$		-	4	6	
Fall time	t_f		-	2	3	
Turn-on delay time	$t_{d(on)}$	V_{DD} = -10 V, R_L = 2.3 Ω I_D ≅ -4.3 A, V_{GEN} = -8 V, R_g = 1 Ω	-	0.09	0.14	
Rise time	t_r		-	0.4	0.6	
Turn-off delay time	$t_{d(off)}$		-	5.2	7.8	
Fall time	t_f		-	2.3	3.5	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	T_C = 25 °C	-	-	-1.5	A
Pulse diode forward current	I_{SM}		-	-	-20	
Body diode voltage	V_{SD}	I_S = -3 A, V_{GS} = 0 V	-	-0.8	-1.2	V
Body diode reverse recovery time	t_{rr}	I_F = -3 A, di/dt = 100 A/µs, T_J = 25 °C	-	30	60	ns
Body diode reverse recovery charge	Q_{rr}		-	20	40	nC
Reverse recovery fall time	t_a		-	13	-	ns
Reverse recovery rise time	t_b		-	17	-	

Notes

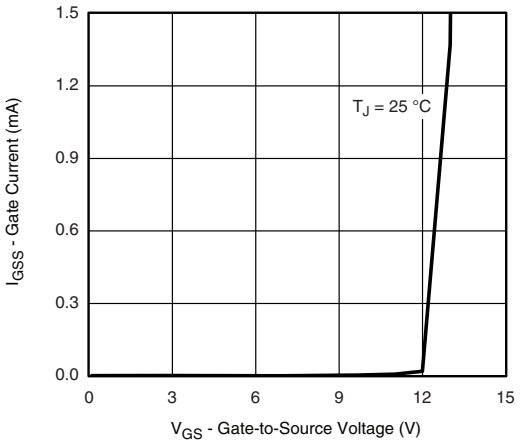
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%

b. Guaranteed by design, not subject to production testing

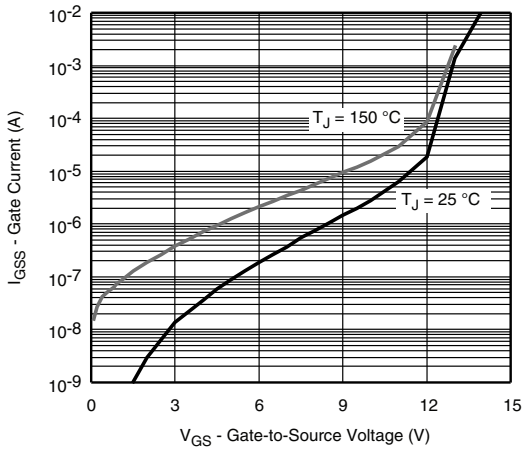
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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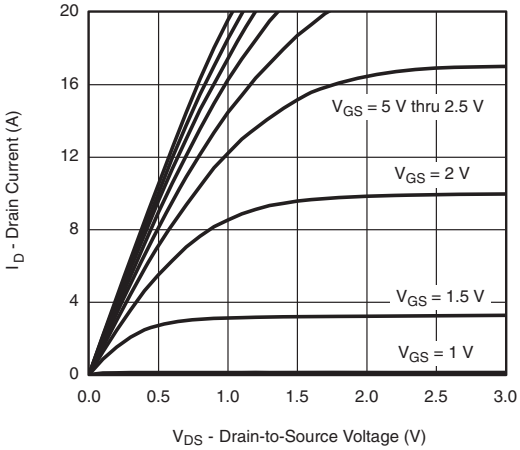
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



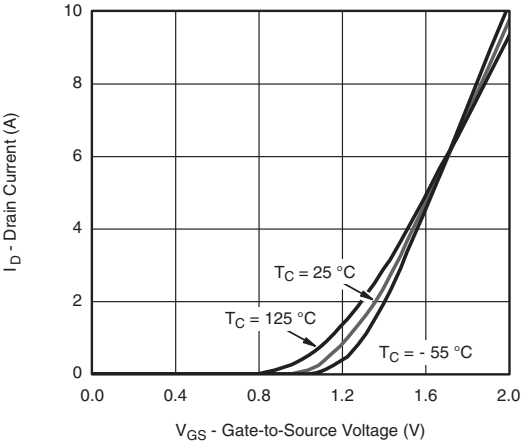
Gate Current vs. Gate-Source Voltage



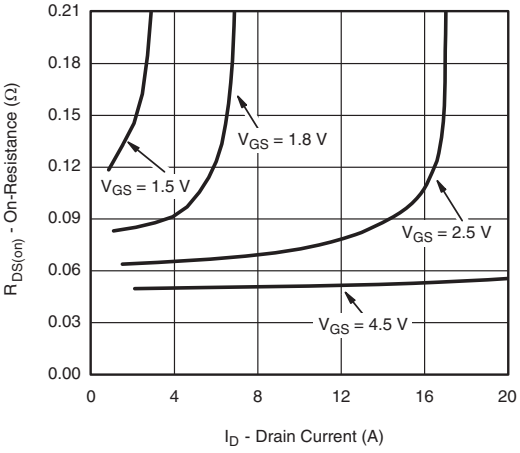
Gate Current vs. Gate-Source Voltage



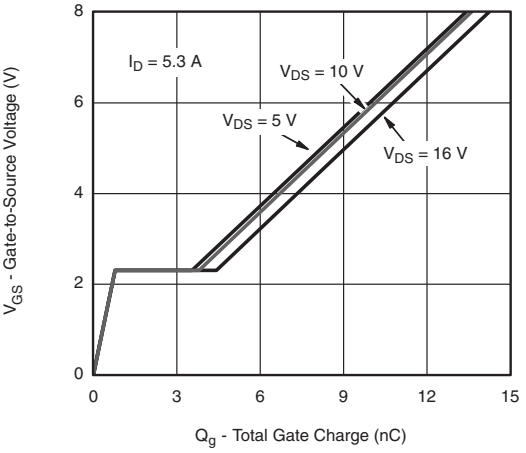
Output Characteristics



Transfer Characteristics



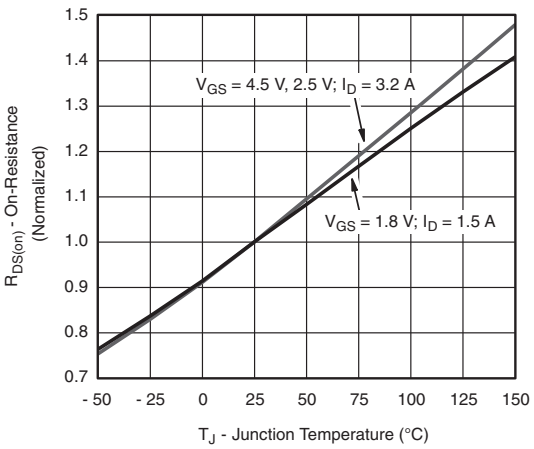
On-Resistance vs. Drain Current



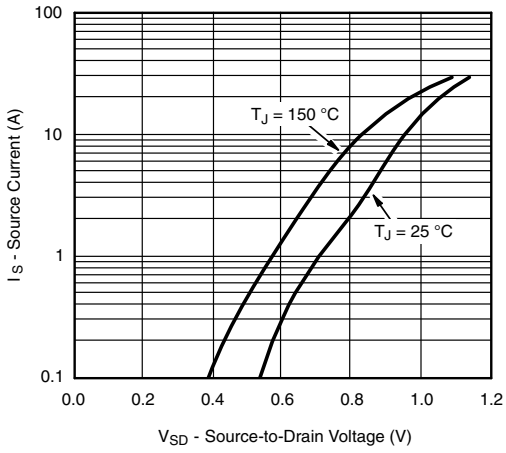
Gate Charge

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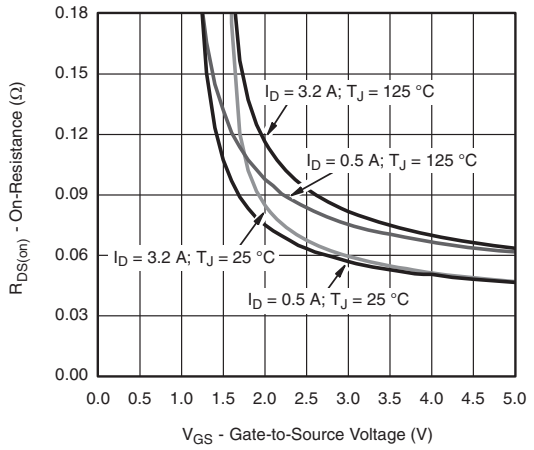
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



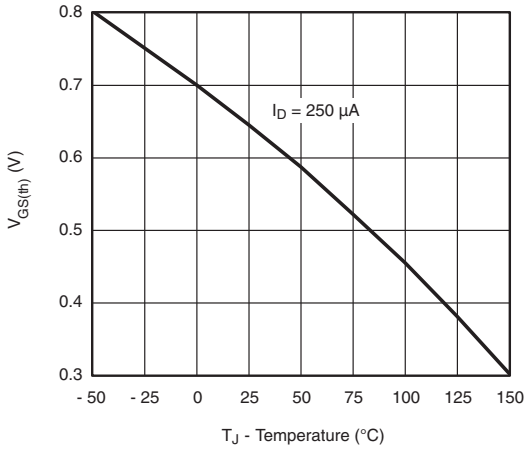
On-Resistance vs. Junction Temperature



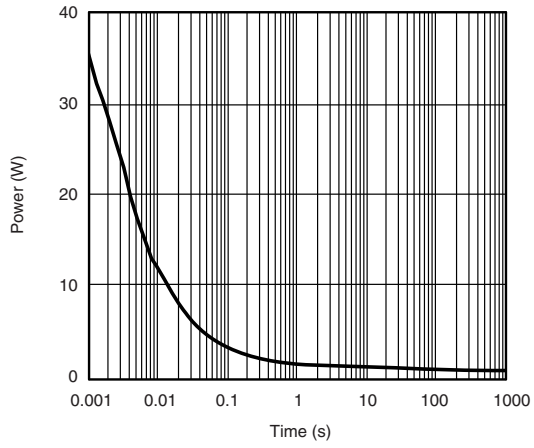
Source-Drain Diode Forward Voltage



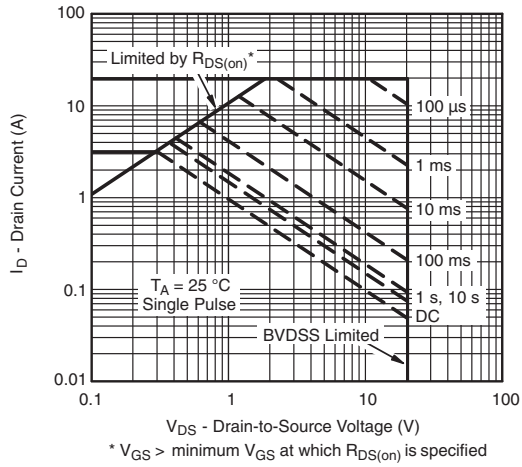
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



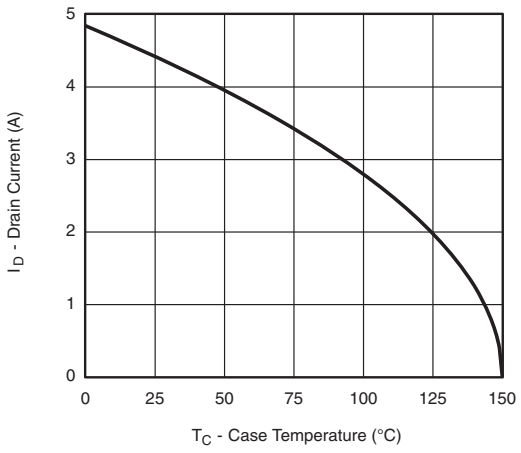
Single Pulse Power, Junction-to-Ambient



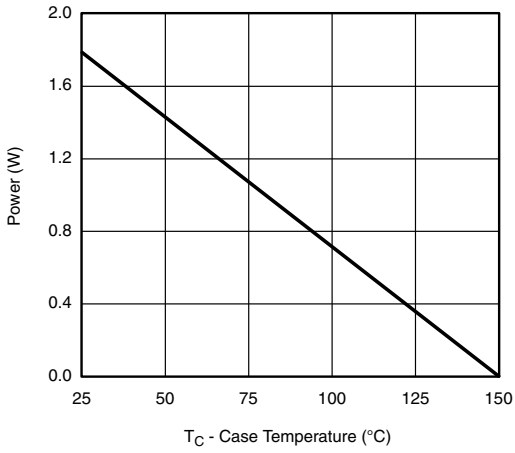
Safe Operating Area, Junction-to-Ambient

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating [a]



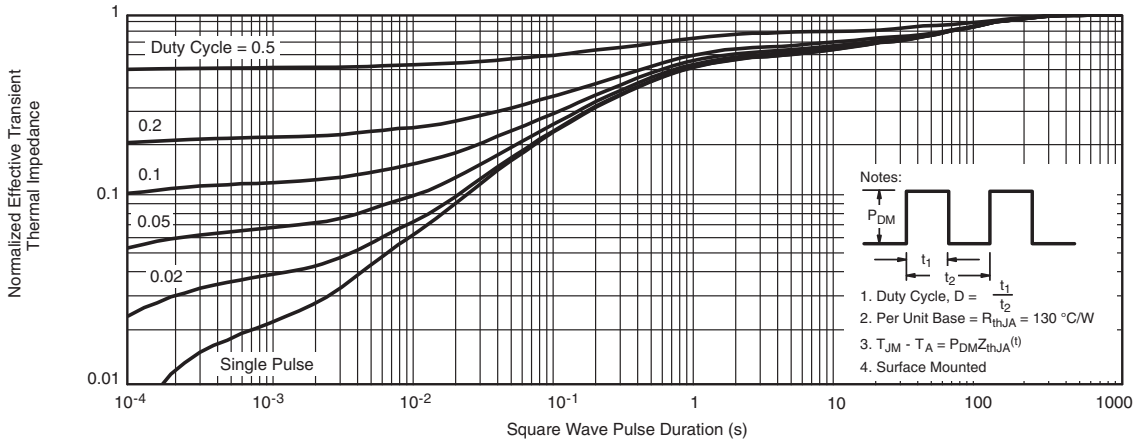
Power Derating

Note

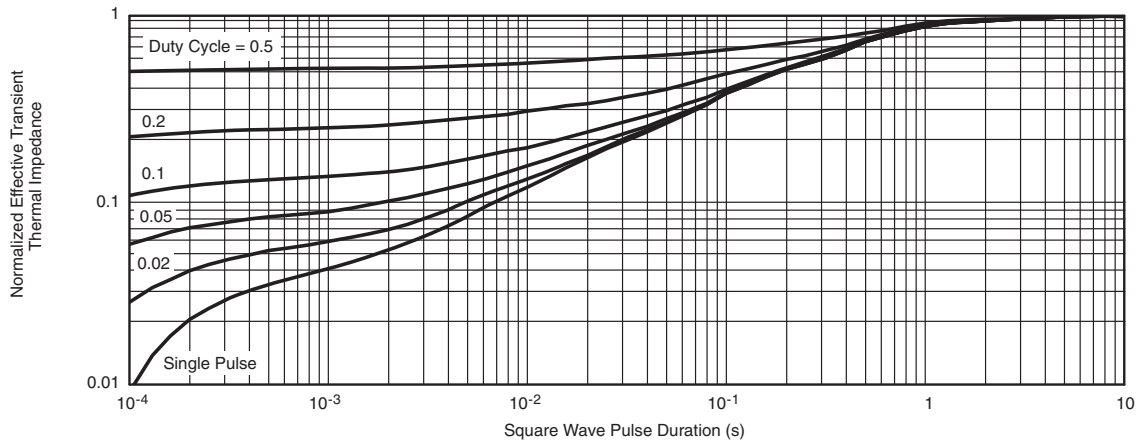
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

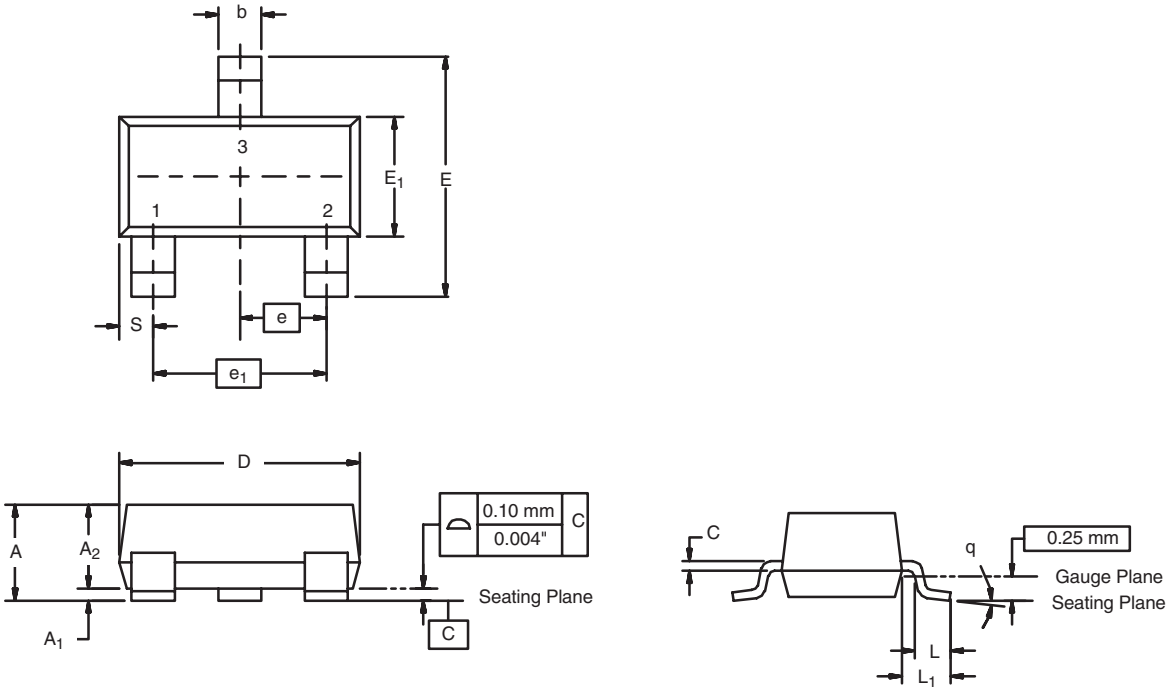


Normalized Thermal Transient Impedance, Junction-to-Foot

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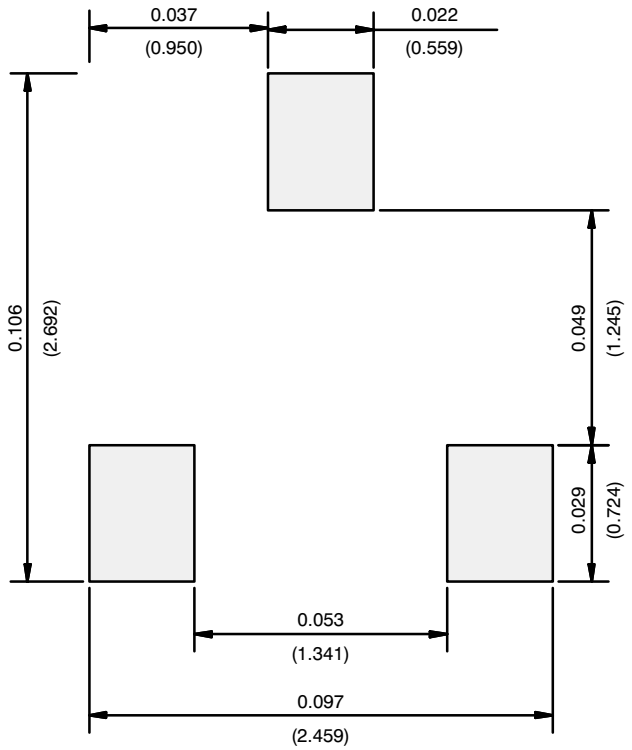
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SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A_1	0.01	0.10	0.0004	0.004
A_2	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E_1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e_1	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L_1	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE

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